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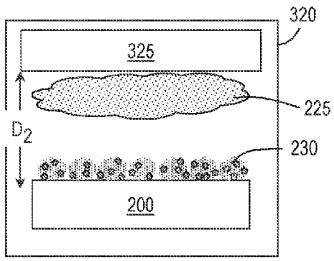


FIG. 2C

(57) Abstract: Methods of depositing an adamantane film are described, which may be used in the manufacture of integrated circuits. Methods include processing a substrate in which an adamantane seed layer is deposited on a substrate, converting to a diamond nuclei layer having an increased crystallinity relative to the adamantane seed layer and then grown into full nanocrystalline diamond film from the diamond nuclei layer.

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